

ABSTRACT

SiC INGOT FORMING METHOD

An SiC ingot forming method includes: a holding step of holding by a chuck table a cut section of a primitive SiC ingot cut from an SiC ingot growth base; a planarization step of grinding an end surface of the primitive SiC ingot held by the chuck table, to planarize the end surface; a c-plane detection step of detecting a c-plane of the primitive SiC ingot from the planarized end surface; a first end surface forming step of grinding the planarized end surface, to form a first end surface inclined at an off angle relative to the c-plane; and a second end surface forming step of holding the first end surface by the chuck table and grinding the cut section of the primitive SiC ingot in parallel to the first end surface, to form a second end surface.

(Figure 5B)